

DIODE SPECIFICATION

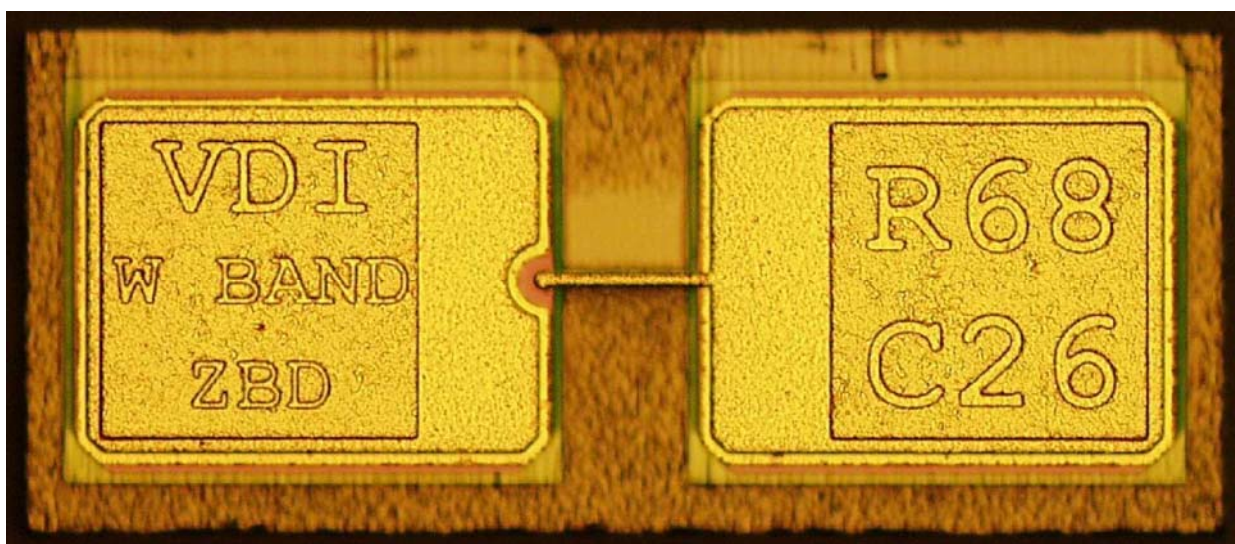
W Band ZBD

Table I ELECTRICAL CHARACTERISTICS

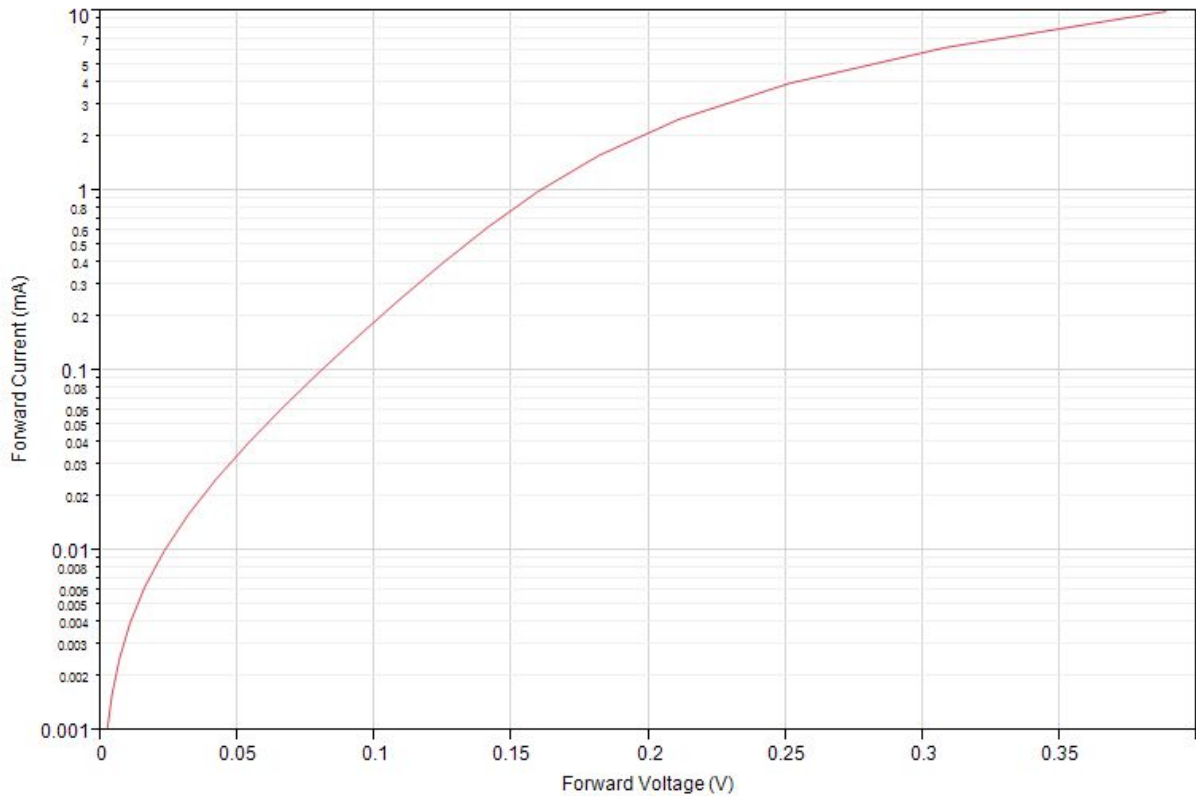
	Test Conditions	Minimum Value	Maximum Value	Units
V _F Forward Turn-on Voltage	I _F = 100 μA	45	95	mV
ΔV	1 mA – 100 μA	65	90	mV
I _{sat} Saturation Current		5	35	μA
R _v Video Resistance		1000	5000	Ω
C _T Total Capacitance			25	fF
C _{PP} Pad to Pad Capacitance	V = 0V		15	fF

Table II PHYSICAL DIMENSIONS

	Minimum Value	Maximum Value	Units
Chip Length	580	600	μm
Chip Width	230	250	μm
Substrate Thickness	40	55	μm



Typical Forward IV Curve



The following are explanations of the parameters listed above in the diode specification:

- V_f Forward Turn-on Voltage = Voltage measured at either 100 μ A forward current
- ΔV = Voltage measured at 1 mA forward current - Voltage measured at 100 μ A forward current
- I_{sat} Saturation Current and R_v Video Resistance are calculated from IV curves